

# IRF7488PbF

HEXFET® Power MOSFET

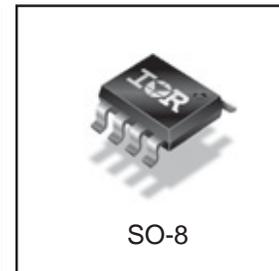
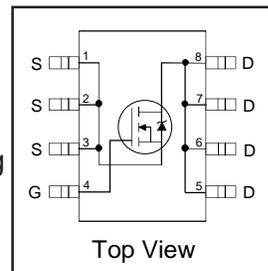
## Applications

- High frequency DC-DC converters
- Lead-Free

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max</b>	<b>Q<sub>g</sub></b>
<b>80V</b>	<b>29mΩ@V<sub>GS</sub>=10V</b>	<b>38nC</b>

## Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>OSS</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



## Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	80	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	6.3	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	5.0	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	50	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Maximum Power Dissipation	2.5	W
P <sub>D</sub> @ T <sub>A</sub> = 70°C	Maximum Power Dissipation	1.6	
	Linear Derating Factor	20	mW/°C
T <sub>J</sub>	Operating Junction and Storage Temperature Range	-55 to + 150	°C
T <sub>STG</sub>	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

## Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJL</sub>	Junction-to-Drain Lead	—	20	°C/W
R <sub>θJA</sub>	Junction-to-Ambient <sup>④</sup>	—	50	

Notes <sup>①</sup> through <sup>④</sup> are on page 9  
www.irf.com

# IRF7488PbF

International  
IR Rectifier

## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	80	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.089	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA ③
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	24	29	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.8A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -20V

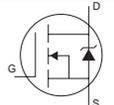
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

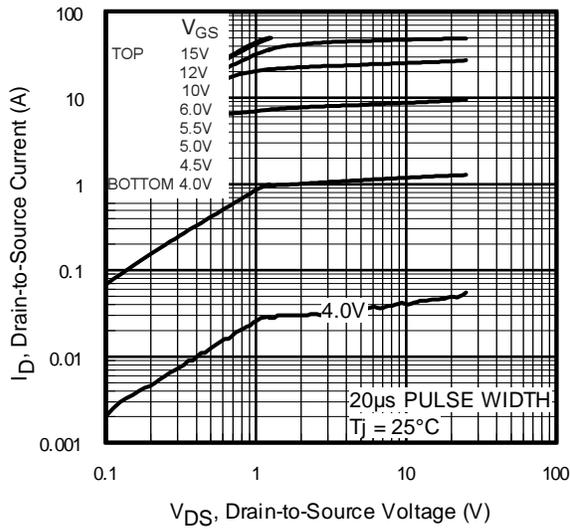
	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	9.3	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 3.8A
Q <sub>g</sub>	Total Gate Charge	—	38	57	nC	I <sub>D</sub> = 3.8A
Q <sub>gs</sub>	Gate-to-Source Charge	—	9.1	—		V <sub>DS</sub> = 40V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	12	—		V <sub>GS</sub> = 10V,
t <sub>d(on)</sub>	Turn-On Delay Time	—	13	—	ns	V <sub>DD</sub> = 40V
t <sub>r</sub>	Rise Time	—	12	—		I <sub>D</sub> = 3.8A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	44	—		R <sub>G</sub> = 9.1Ω
t <sub>f</sub>	Fall Time	—	16	—		V <sub>GS</sub> = 10V ③
C <sub>iss</sub>	Input Capacitance	—	1680	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	270	—		V <sub>DS</sub> = 25V
C <sub>riss</sub>	Reverse Transfer Capacitance	—	32	—		f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	1760	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	170	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 64V, f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance	—	340	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 64V ⑤

## Avalanche Characteristics

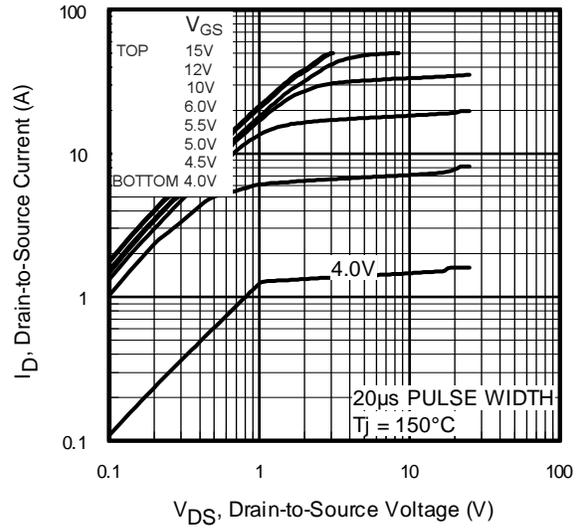
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	96	mJ
I <sub>AR</sub>	Avalanche Current①	—	3.8	A

## Diode Characteristics

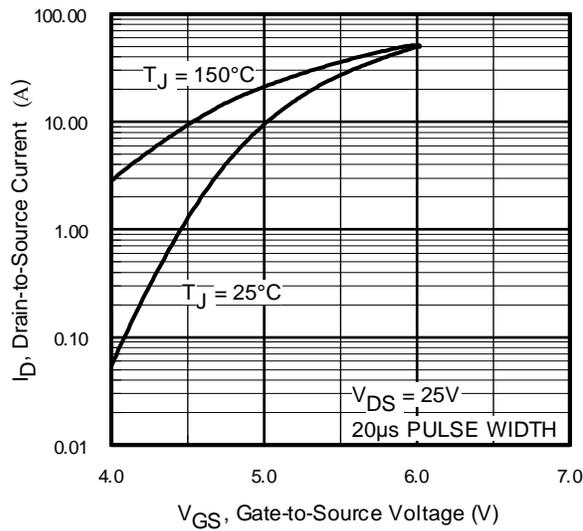
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	50		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 3.8A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	65	98	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 3.8A
Q <sub>rr</sub>	Reverse Recovery Charge	—	190	290	nC	di/dt = 100A/μs ③



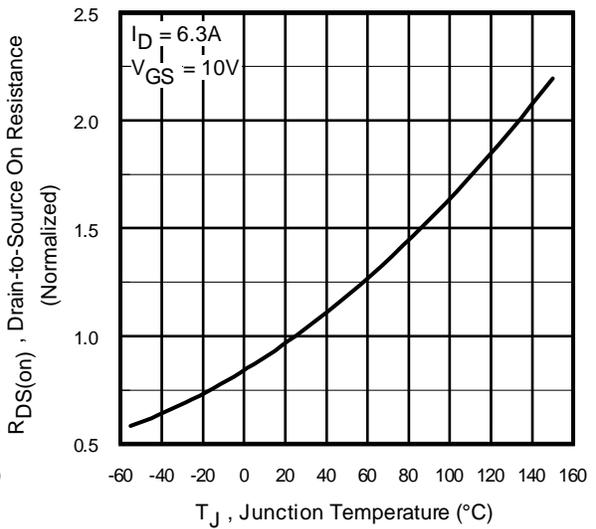
**Fig 1.** Typical Output Characteristics



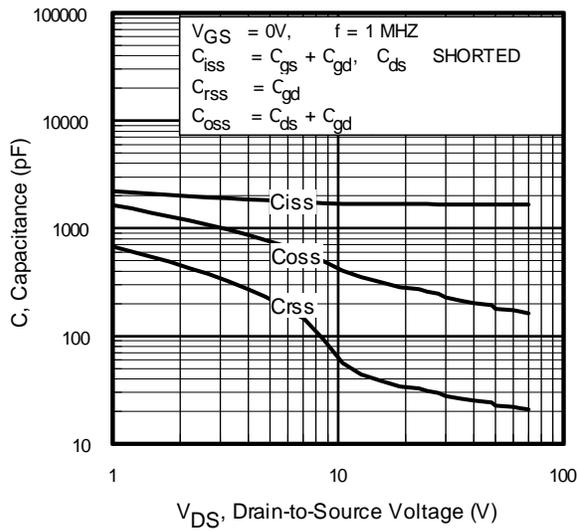
**Fig 2.** Typical Output Characteristics



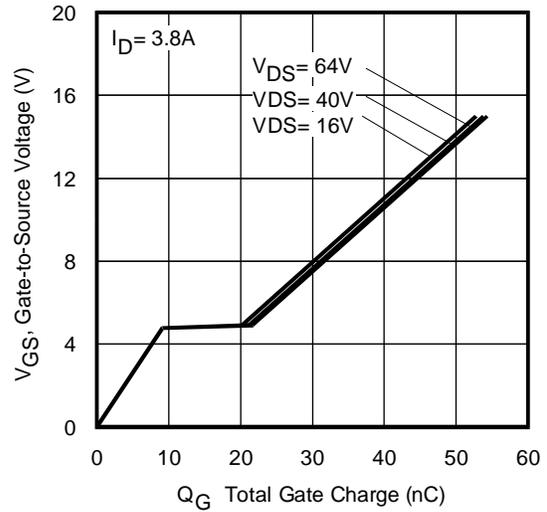
**Fig 3.** Typical Transfer Characteristics



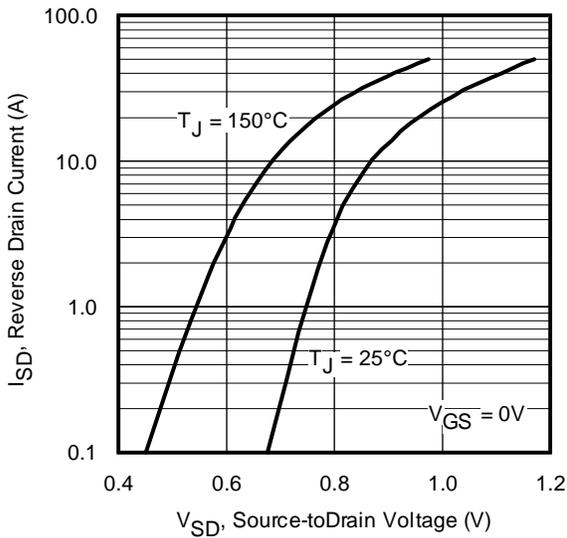
**Fig 4.** Normalized On-Resistance Vs. Temperature



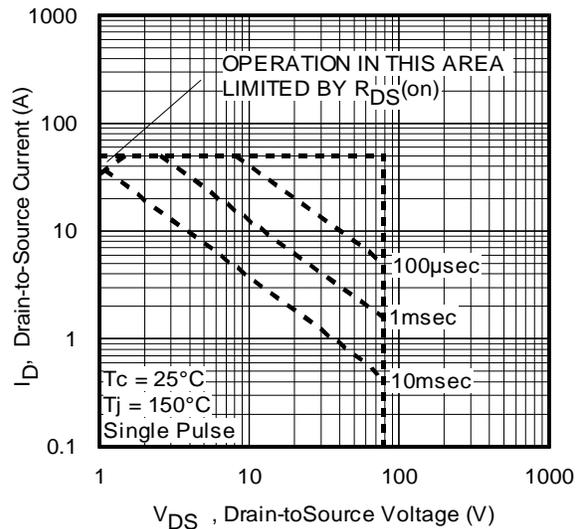
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



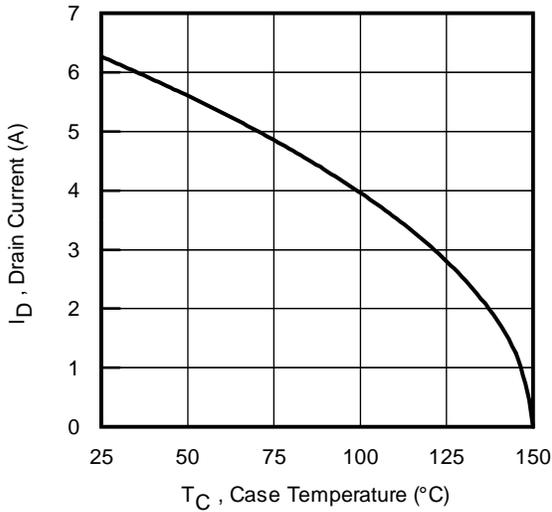
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



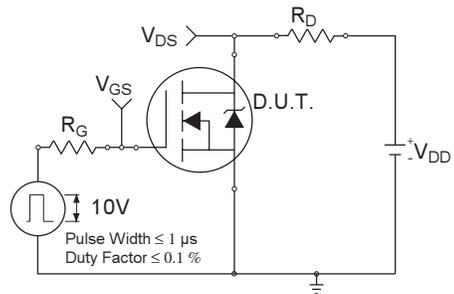
**Fig 7.** Typical Source-Drain Diode Forward Voltage



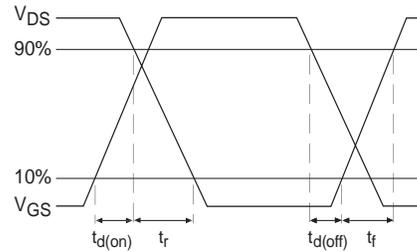
**Fig 8.** Maximum Safe Operating Area



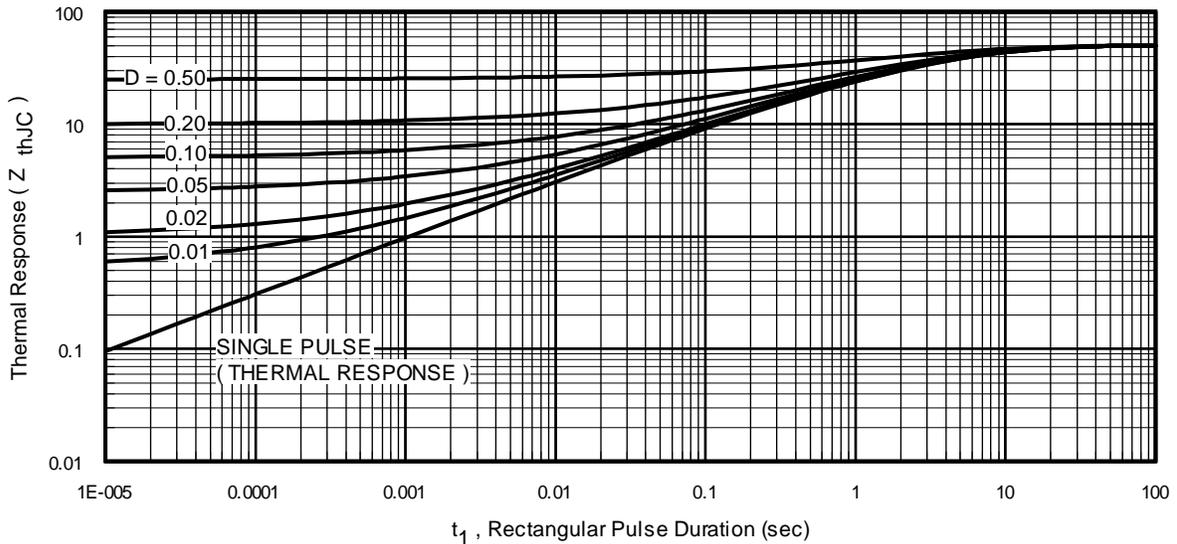
**Fig 9.** Maximum Drain Current Vs. Ambient Temperature



**Fig 10a.** Switching Time Test Circuit



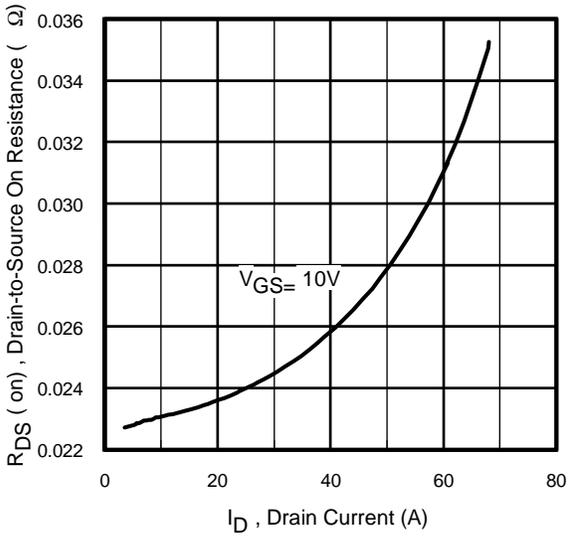
**Fig 10b.** Switching Time Waveforms



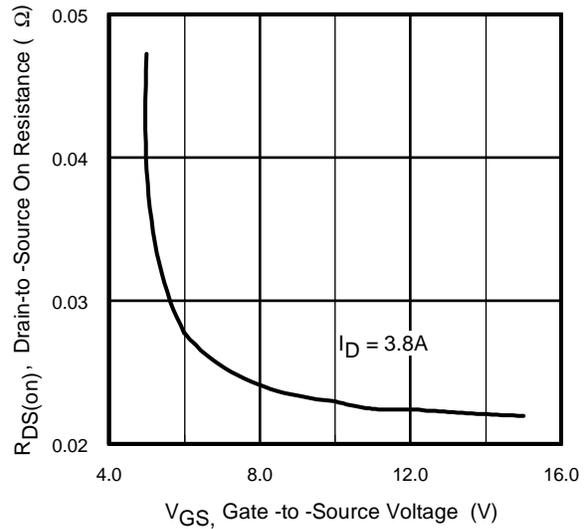
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

# IRF7488PbF

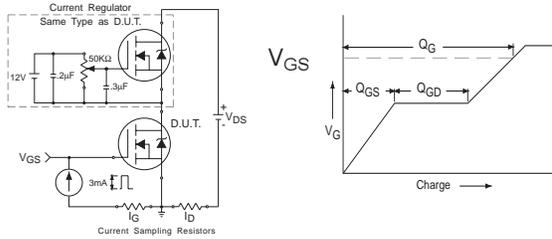
International  
**IR** Rectifier



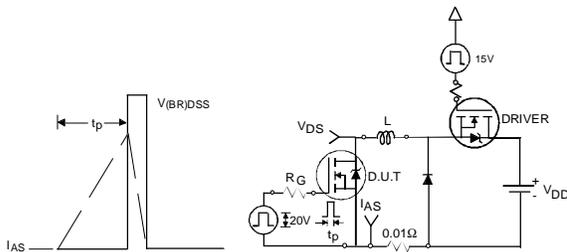
**Fig 12.** On-Resistance Vs. Drain Current



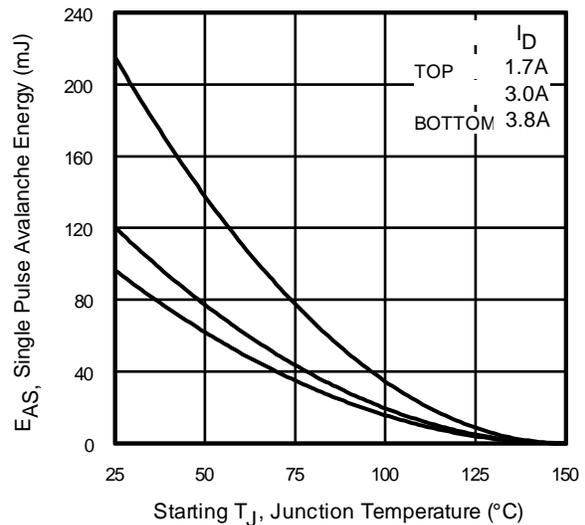
**Fig 13.** On-Resistance Vs. Gate Voltage



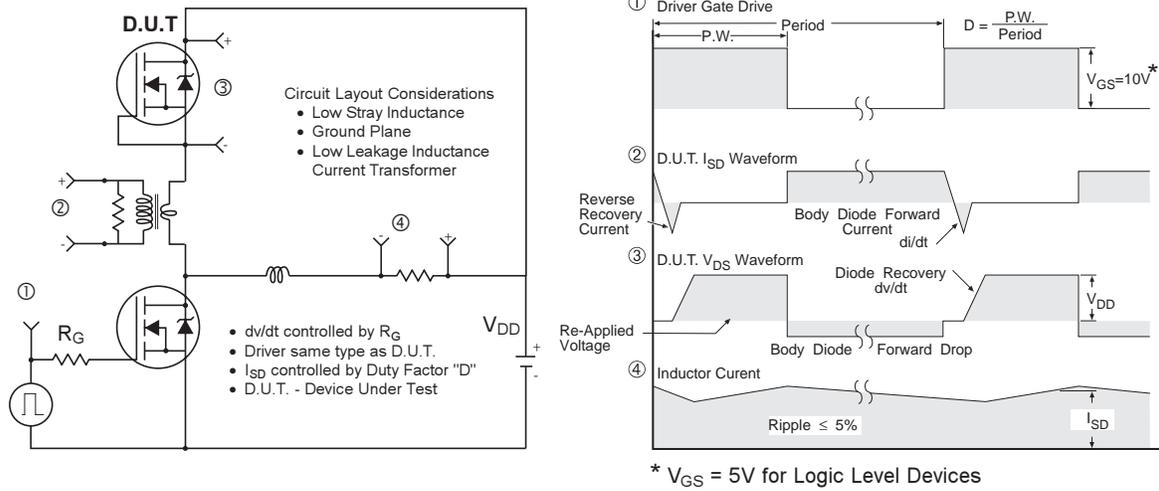
**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform



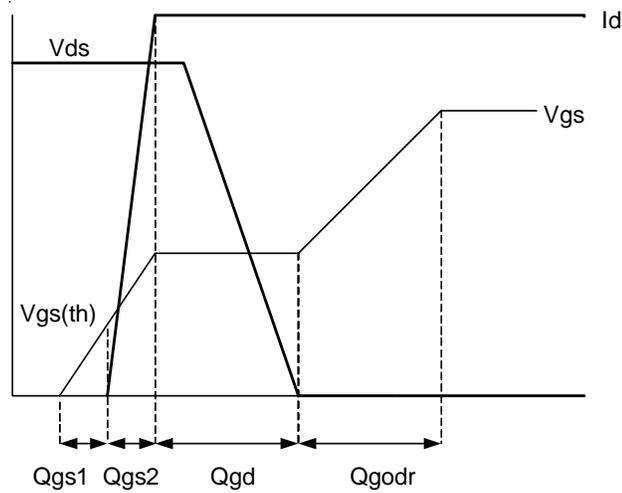
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



**Fig 15c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 16. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**

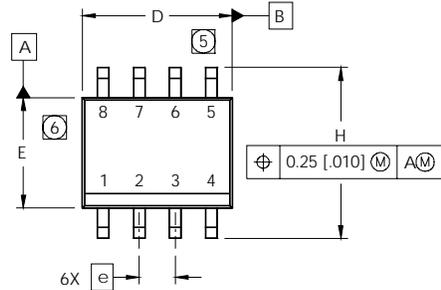


**Fig 17. Gate Charge Waveform**

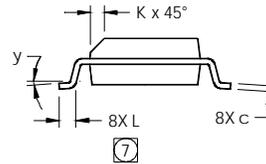
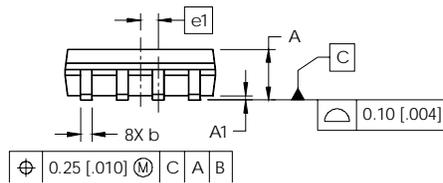
# IRF7488PbF

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



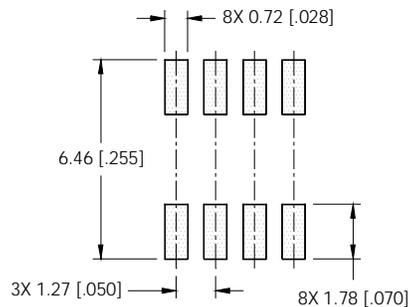
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



### NOTES:

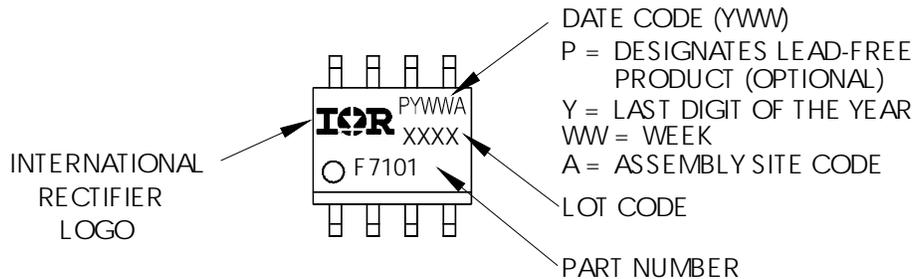
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

### FOOTPRINT



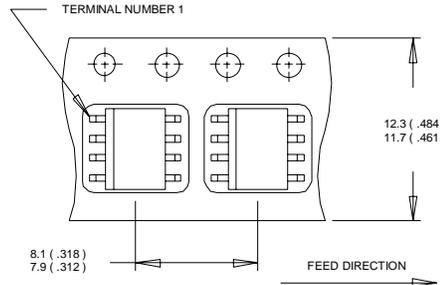
## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

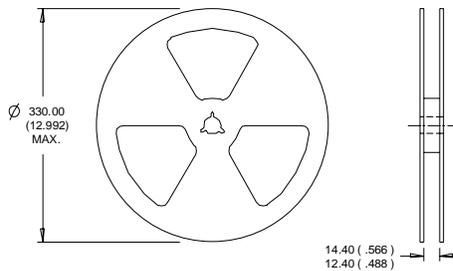


**SO-8 Tape and Reel**

**IRF7488PbF**



NOTES:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).  
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 13\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 3.8\text{A}$ .
- ③ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Consumer market.  
 Qualifications Standards can be found on IR's Web site.

# AMEYA360

## Components Supply Platform

Authorized Distribution Brand :



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➤ Address :

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➤ Sales :

Direct +86 (21) 6401-6692

Email [amall@ameya360.com](mailto:amall@ameya360.com)

QQ 800077892

Skype [ameyasales1](#) [ameyasales2](#)

➤ Customer Service :

Email [service@ameya360.com](mailto:service@ameya360.com)

➤ Partnership :

Tel +86 (21) 64016692-8333

Email [mkt@ameya360.com](mailto:mkt@ameya360.com)